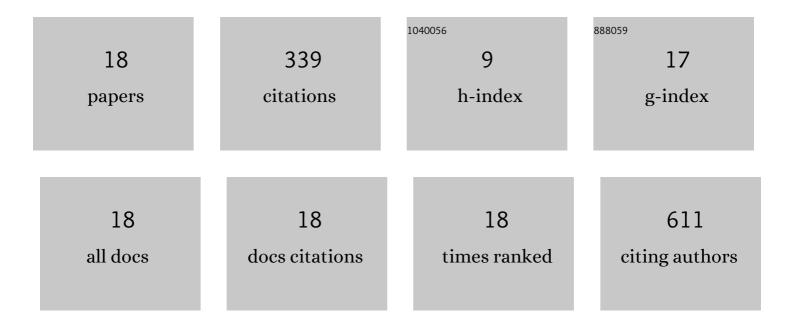
Takahiko Endo

List of Publications by Year in descending order

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Τλέλμικο Ενίδο

#	Article	IF	CITATIONS
1	Chemically Tuned p―and nâ€Type WSe ₂ Monolayers with High Carrier Mobility for Advanced Electronics. Advanced Materials, 2019, 31, e1903613.	21.0	111
2	Restoring the intrinsic optical properties of CVD-grown MoS ₂ monolayers and their heterostructures. Nanoscale, 2019, 11, 12798-12803.	5.6	37
3	Gas-Source CVD Growth of Atomic Layered WS2 from WF6 and H2S Precursors with High Grain Size Uniformity. Scientific Reports, 2019, 9, 17678.	3.3	36
4	Momentum-forbidden dark excitons in hBN-encapsulated monolayer MoS2. Npj 2D Materials and Applications, 2019, 3, .	7.9	25
5	Directional Exciton-Energy Transport in a Lateral Heteromonolayer of WSe ₂ –MoSe ₂ . ACS Nano, 2022, 16, 8205-8212.	14.6	20
6	Wafer-Scale Growth of One-Dimensional Transition-Metal Telluride Nanowires. Nano Letters, 2021, 21, 243-249.	9.1	18
7	Versatile Post-Doping toward Two-Dimensional Semiconductors. ACS Nano, 2021, 15, 19225-19232.	14.6	14
8	Air-stable and efficient electron doping of monolayer MoS ₂ by salt–crown ether treatment. Nanoscale, 2021, 13, 8784-8789.	5.6	12
9	Control of Thermal Conductance across Vertically Stacked Two-Dimensional van der Waals Materials <i>via</i> Interfacial Engineering. ACS Nano, 2021, 15, 15902-15909.	14.6	11
10	Dynamical symmetry of strongly light-driven electronic system in crystalline solids. Communications Physics, 2020, 3, .	5.3	10
11	Synthesis and ambipolar transistor properties of tungsten diselenide nanotubes. Applied Physics Letters, 2020, 116, .	3.3	10
12	Spatial Control of Dynamic <i>p–i–n</i> Junctions in Transition Metal Dichalcogenide Light-Emitting Devices. ACS Nano, 2021, 15, 12911-12921.	14.6	8
13	Monolayer MoS2 growth at the Au–SiO2 interface. Nanoscale, 2019, 11, 19700-19704.	5.6	7
14	Nanowire-to-Nanoribbon Conversion in Transition-Metal Chalcogenides: Implications for One-Dimensional Electronics and Optoelectronics. ACS Applied Nano Materials, 2022, 5, 1775-1782.	5.0	7
15	Chemical Doping: Chemically Tuned p―and nâ€īype WSe ₂ Monolayers with High Carrier Mobility for Advanced Electronics (Adv. Mater. 42/2019). Advanced Materials, 2019, 31, 1970301.	21.0	4
16	ALD-ZrO ₂ gate dielectric with suppressed interfacial oxidation for high performance MoS ₂ top gate MOSFETs. Japanese Journal of Applied Physics, 2021, 60, SBBH03.	1.5	4
17	Formation of a Two-Dimensional Electronic System in Laterally Assembled WTe Nanowires. ACS Applied Nano Materials, 2022, 5, 6277-6284.	5.0	4
18	Comparative Study of High-k Dielectric on MoS2 Deposited by Plasma Enhanced ALD. , 2019, , .		1